

Appl. No. 09/821,636
Amdt. Dated August 12, 2005
Reply to Office Action of March 28, 2005

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A display apparatus comprising:

a plurality of thin film transistors, each of said thin film transistor comprising a semiconductor thin film constituting a channel and having a threshold voltage, and a first gate electrode on one side of said semiconductor thin film and a second gate electrode on an opposite side of said semiconductor thin film,

and further comprising a means for adjusting the threshold voltage by applying a first threshold adjustment voltage to the second gate electrode when the first gate electrode receives a first control voltage and applying a second threshold adjustment voltage different than the first threshold adjustment voltage to the second gate electrode when the first electrode receives a second control voltage ~~and wherein the voltage applied to the first gate electrode is different from the threshold adjustment voltage applied to the second gate electrode each during voltage application.~~

2. (Currently Amended) The semiconductor apparatus according to claim 1, wherein said semiconductor thin film constituting said channel is comprised of polycrystalline silicon which does not contain an impurity affecting the formation of a depletion layer, and has a thickness of 100 nm or less.

Appl. No. 09/821,636
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3. (Original) The semiconductor apparatus according to claim 1, wherein said semiconductor thin film constituting said channel is comprised of polycrystalline silicon which contains an impurity effectively affecting the formation of a depletion layer, and has a thickness two times or less the maximum of the thickness of said depletion layer.

Claims 4-38 (Canceled).

39. (Currently Amended) A display apparatus comprising:

a plurality of thin film transistors, each of said thin film transistor comprising a semiconductor thin film constituting a channel and having a threshold voltage, and a first gate electrode above said semiconductor thin film and a second gate electrode below said semiconductor thin film,

and further comprising a means for adjusting the threshold voltage by applying a first threshold adjustment voltage to the second gate electrode when the first gate electrode receives a first control voltage and applying a second threshold adjustment voltage, different than the first threshold adjustment voltage, to the second gate electrode when the first electrode receives a second control voltage ~~and wherein the voltage applied to the first gate electrode is different from the threshold adjustment voltage applied to the second gate electrode during voltage application.~~

page 3 of 6

Appl. No. 09/821,636
Amdt. Dated August 12, 2005
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Please add the following new claims:

40. (New) A display apparatus according to claim 1, further wherein the voltage applied to the first gate electrode is different from the threshold adjustment voltage applied to the second gate electrode during voltage application.

41. (New) A display apparatus according to claim 39, further wherein the voltage applied to the first gate electrode is different from the threshold adjustment voltage applied to the second gate electrode during voltage application.